

Silicon NPN Power Transistors

2SD1243

DESCRIPTION

www.datasheet4u.com

- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

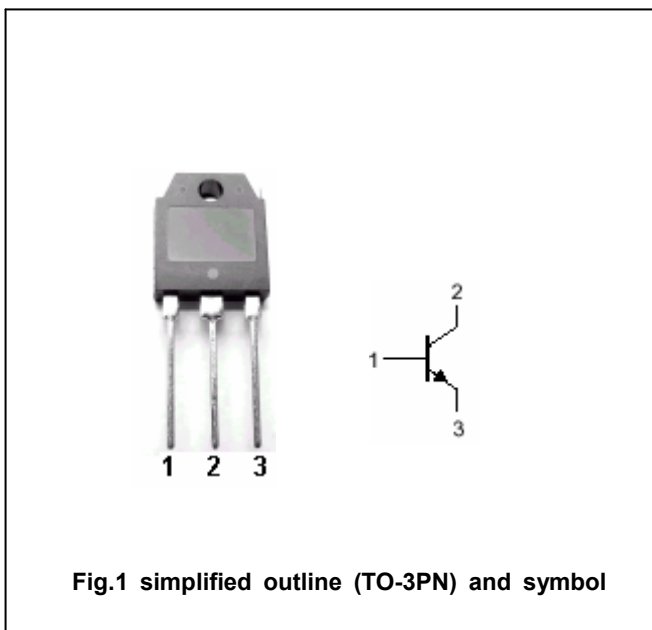


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
I _{CM}	Collector current-peak		15	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50\text{mA}; I_B=0$	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1\text{mA}; I_E=0$	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=60\text{V}; I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=3\text{A}; V_{CE}=3\text{V}$	50			

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PACKAGE OUTLINE

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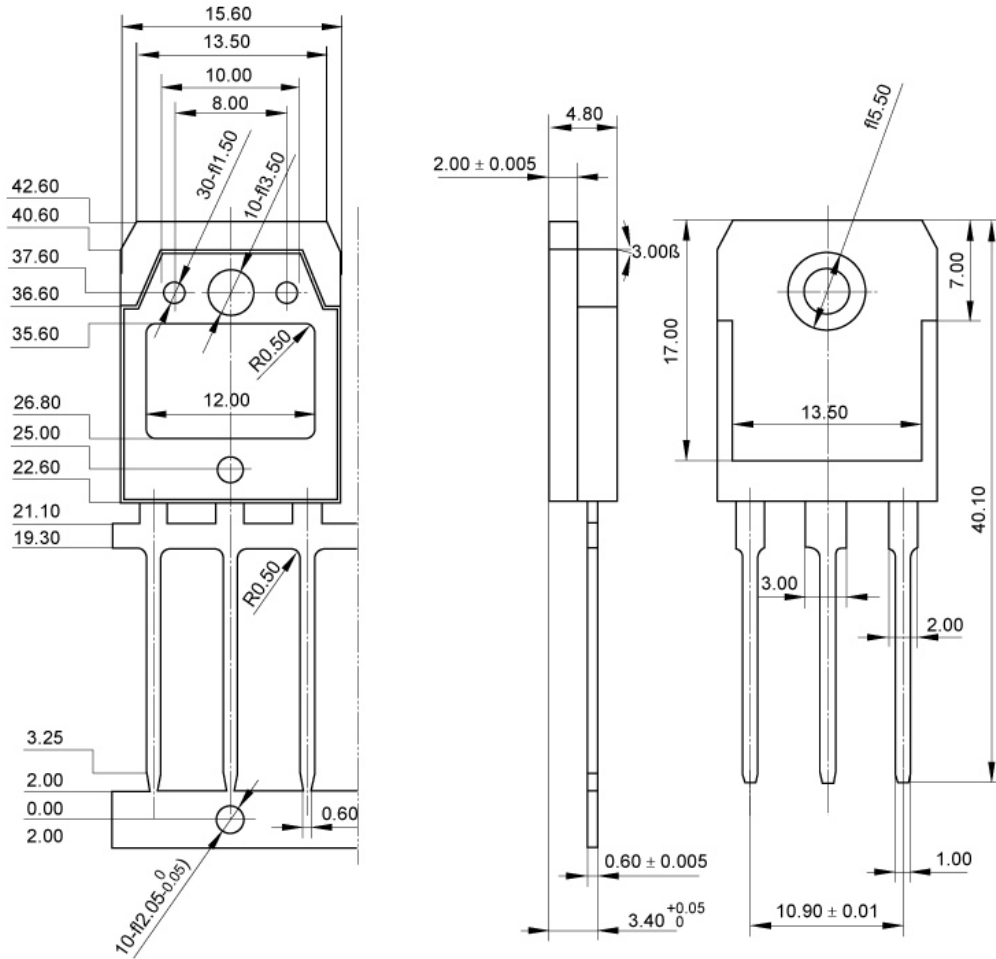


Fig.2 outline dimensions